$I_{FAV} = 2x \cdot 40 A$

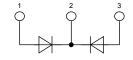
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HiPerFRED²

High Performance Fast Recovery Diode Low Loss and Soft Recovery Common Cathode

Part number

DPG 80 C 400 HB



1 3

400 V

45 ns

Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

 $V_{RRM} =$

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}C$			400	V
I _R	reverse current	V _R = 400 V	$T_{VJ} = 25^{\circ}C$			1	μΑ
		$V_R = 400 V$	$T_{VJ} = 150$ °C			0.4	mA
V _F	forward voltage	I _F = 40 A	$T_{VJ} = 25^{\circ}C$			1.43	V
		$I_F = 80 A$				1.77	V
		I _F = 40 A	T _{VJ} = 150°C			1.14	V
		$I_F = 80 A$				1.51	V
I _{FAV}	average forward current	rectangular d = 0.5	$T_{c} = 135^{\circ}C$			40	Α
V _{F0}	threshold voltage	adaulation only	T _{VJ} = 175°C			0.79	V
r _F	slope resistance	calculation only				7.1	mΩ
R _{thJC}	thermal resistance junction to case					0.70	K/W
T _{VJ}	virtual junction temperature			-55		175	°C
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			215	W
I _{FSM}	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			400	Α
I _{RM}	max. reverse recovery current		T _{VJ} = 25°C		4		Α
		$I_F = 40 \text{ A}; V_R = 100 \text{ V}$	$T_{VJ} = ^{\circ}C$		tbd		Α
t _{rr}	reverse recovery time	$-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		45		ns
			$T_{VJ} = ^{\circ}C$		tbd		ns
C _J	junction capacitance	$V_R = 200 \text{ V}; f = 1 \text{ MHz}$	T _{VJ} = 25°C		46		pF



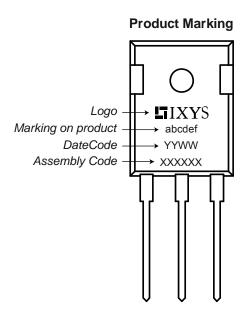
Ratings



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				Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit		
I _{RMS}	RMS current	per pin 1)			70	Α		
R _{thCH}	thermal resistance case to heatsink			0.25		K/W		
T _{stg}	storage temperature		-55		150	°C		
Weight				6		g		
M _D	mounting torque		0.8		1.2	Nm		
F _c	mounting force with clip		20		120	N		

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip. In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



Part number

D = Diode

P = HiPerFRED

G = extreme fast

80 = Current Rating [A]

C = Common Cathode

400 = Reverse Voltage [V]

HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key		
Standard	DPG 80 C 400 HB	DPG80C400HB	Tube	30	506875		



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